

IN THE CLAIMS

Claims 1-13 (Canceled).

14 (Previously Presented). A process comprising:
forming a recess having a bottom and a wall;
forming an electrically resistive film in the recess to form a heater; and
treating the film to have different electrical conductivity at the bottom and the wall; and
forming a phase change material over said wall.

15 (Currently Amended). The process according to claim 14, wherein treating includes implanting the ~~polysilicon~~ film at a first angle and implanting the polysilicon film at a second angle different from the first angle.

16 (Previously Presented). The process according to claim 14, wherein treating further comprises doping the film to form discrete isolated regions.

17 (Previously Presented). The process according to claim 14, before treating, further comprising:
forming a temporary material in the recess; and
patterning the temporary material to expose the film.

18 (Previously Presented). The process according to claim 14, before treating, further comprising:
forming a temporary material in the recess;
patterning a mask over the temporary material; and
removing a portion of the temporary material to expose the film.

Claims 19-34 (Canceled).

35 (Currently Amended). A method comprising:
forming a recess in a dielectric layer;
forming a heater material ~~in~~ over said recess to form a wall including an edge; and
forming a phase change material over said heater material, the phase change material in contact with said edge.

36 (Previously Presented). The method of claim 35 including forming said heater of polysilicon film.

37 (Previously Presented). The method of claim 35 including forming a resistive film by deposition over said recess.

38 (Previously Presented). The method of claim 35 including implanting selected regions of said film to create regions of different electrical conductivity within said film.

39 (Previously Presented). The method of claim 35 including forming said heater material in a U-shape.

40 (Previously Presented). The method of claim 39 including filling said U-shaped heater material with a dielectric material.

41 (Previously Presented). The method of claim 40 wherein said U-shaped heater includes a base and an upstanding wall having said edge spaced away from said base.

42 (Previously Presented). The method of claim 35 including covering said recess and said dielectric layer with said heater material.

43 (Previously Presented). The method of claim 42 including planarizing said heater material.

44 (Previously Presented). The method of claim 43 including removing said heater material from over said dielectric layer.

45 (Previously Presented). The method of claim 35 including forming said recess completely through said dielectric layer.